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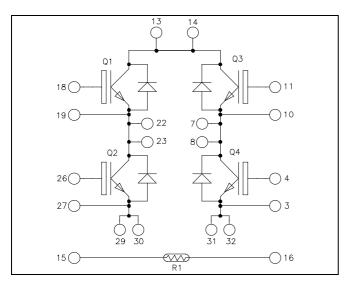


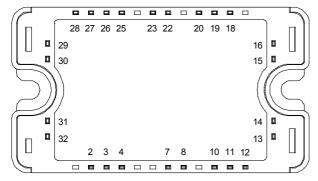






Full - Bridge Trench + Field Stop IGBT3 Power Module





All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

$V_{CES} = 1700V$ $I_C = 30A$ @ $T_C = 80^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
T	Continuous Collector Current	$T_C = 25^{\circ}C$	45	
I_{C}	Continuous Collector Current	$T_C = 80$ °C	30	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	70	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	210	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	60A@1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		2.0	2.4	V
$V_{CE(sat)}$		$I_{\rm C} = 30 {\rm A}$ $T_{\rm j} = 125 {\rm ^{\circ}C}$		2.4		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.5 \text{mA}$		5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		2500		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		90		pr
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		100		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		70		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 900V$ $I_{\text{C}} = 30A$		650		ns
$T_{\rm f}$	Fall Time	$R_G = 18\Omega$		80		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		100		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		70		20.0
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 900V$ $I_C = 30A$		750		ns
$T_{\rm f}$	Fall Time	$R_G = 18\Omega$		100		
Eon	Turn-on Switching Energy	-		17		mJ
E_{off}	Turn-off Switching Energy			15		1113

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_{R}=1700V$	$T_i = 25$ °C $T_i = 125$ °C			250 500	μΑ
I_{F}	DC Forward Current		$T_i = 123 \text{ C}$ $T_C = 80 \text{ °C}$		50	300	A
V_{F}	Diode Forward Voltage	$I_F = 50A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.8	2.2	V
v _F	Diode Polward Voltage		$T_{i} = 125^{\circ}C$		1.9		٧
+	Reverse Recovery Time	$I_{F} = 50A$ $V_{P} = 900V$ T_{j}	$T_j = 25^{\circ}C$		385		ns
t_{rr}			$T_{j} = 125^{\circ}C$		490		
0	Payarga Pagayary Chargo		$T_j = 25$ °C		14		
Q _{rr}	Reverse Recovery Charge		$T_j = 125$ °C		23		μC
E _r	Reverse Recovery Energy		$T_j = 25$ °C		6		I
			$T_{j} = 125^{\circ}C$		12		mJ

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

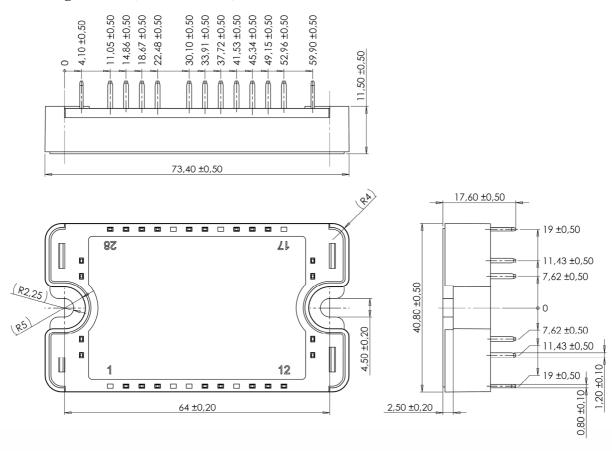
$$R_T: \text{ Thermistor value at T}$$



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT	0.6	0.6	°C/W	
			Diode			0.7	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				110	g	

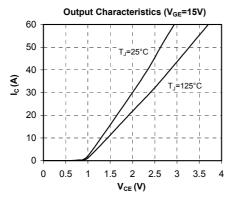
SP3 Package outline (dimensions in mm)

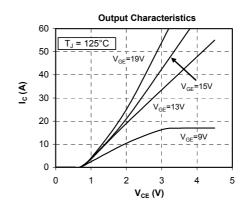


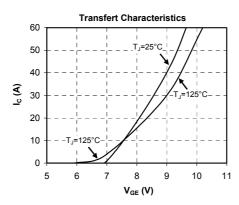
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

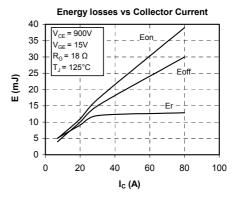


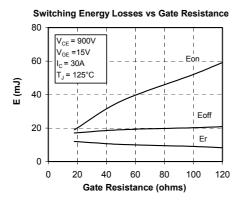
Typical Performance Curve

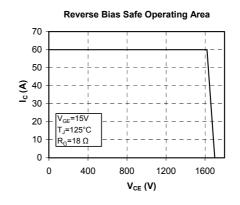


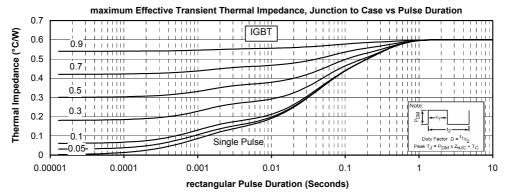




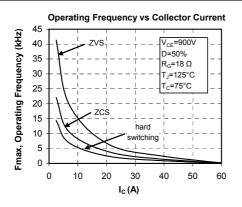


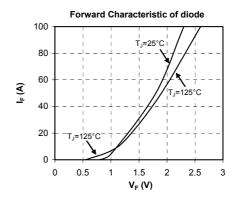


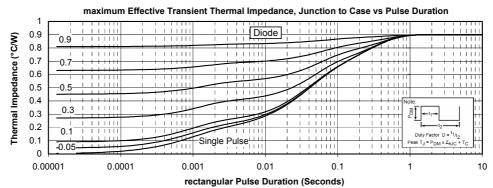












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